

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address ** MMRSSI FREE FEATPAIN AND TEMPERARM GARAGE WAS SPECIAL.

AFFI ICATION NO	HUNG DA H	HRSI NAMED INVENTOR	ATIORNEY DOCKET NO	CONFIRMATION NO	
30 029,144	12/28/2001	Hye Young Kim	265N-0275P	5231	
22%2	8 a) 03 20 2003				
BIRCH STEWART KOLASCH & BIRCH			EXAMINER		
PO BOX 747 FALLS CHUR	CH, VA 22040-0747		QL ZHI QIANG		
			ART UNII	PAPER NUMBER	
			2871		
			DATE MAILED: 03/20/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)	7
Office Action Summary		10/029,144	KIM ET AL.	1
		Examiner	Art Unit	
		Mike Qi	2871	
Period fo	The MAILING DATE of this communication a r Reply	appears on the cover sheet	with the correspondence address	s
THE N - Exter after - If the - If NO - Failui - Any r	DRTENED STATUTORY PERIOD FOR REF MAILING DATE OF THIS COMMUNICATION Issons of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, a in period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by state of the period of the period of the maximum statutory period for reply will, by state of the period of the period of the maximum status of the period of th	N. 1 136(a) In no event, however, may reply within the statutory minimum of to dwill apply and will expire SIX (6) M tute, cause the application to become	a reply be timely filed hirty (30) days will be considered timely ONTHS from the mailing date of this commun ABANDONED (35 U S C § 133)	nication
1)	Responsive to communication(s) filed on _	·		
2a) <u></u> □	This action is FINAL . 2b)⊠	This action is non-final.		
3) Dispositi	Since this application is in condition for allocations of claims			erits is
4)⊡	Claim(s) 1-18 is/are pending in the applicat	ion.		
	4a) Of the above claim(s) is/are withd	lrawn from consideration.		
5)	Claim(s) is/are allowed.			
6)[Claim(s) 1-18 is/are rejected.			
7)	Claim(s) is/are objected to.			
8)	Claim(s) are subject to restriction and	d/or election requirement.		
Applicati	on Papers			
	The specification is objected to by the Exam			
10)	The drawing(s) filed on is/are: a)☐ ac			
	Applicant may not request that any objection to			
11)[The proposed drawing correction filed on		disapproved by the Examiner.	
	If approved, corrected drawings are required in			
12)	The oath or declaration is objected to by the	Examiner.		
Priority L	ınder 35 U.S.C. §§ 119 and 120			
13)[Acknowledgment is made of a claim for fore	eign priority under 35 U.S.C	C. § 119(a)-(d) or (f).	
a)[⊠ All b) Some * c) None of:			
	1. Certified copies of the priority docume	ents have been received.		
	2. Certified copies of the priority docume	ents have been received in	Application No	
* S	3. Copies of the certified copies of the p application from the International see the attached detailed Office action for a l	Bureau (PCT Rule 17.2(a)).	j e
14) 🗌 A	acknowledgment is made of a claim for dome	estic priority under 35 U.S.	C. § 119(e) (to a provisional app	lication).
) The translation of the foreign language Acknowledgment is made of a claim for dome			
Attachmen	t(s)			
2) 🗷 Notic	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449) Paper No(s	5) Notice	w Summary (PTO-413) Paper No(s) of Informal Patent Application (PTO-152	
US Patent and T PTO-326 (Re		Action Summary	Part of Pap	er No. 4

Page 2

Application/Control Number: 10/029,144

Art Unit: 2871

DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1, 4-13, 15-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant admitted prior art in view of US 5,135,581 (Tran et al).

Claims 1 and 13, Applicant admitted prior art discloses (page 1, paragraph 0003 – page 4, paragraph 0012; Figs.1A – 1D) a method of fabricating a pixel electrode and a structure of a pixel electrode in a liquid crystal display comprising:

- a substrate (11);
- a switching device (TFT) for driving the pixel electrode over the substrate
 (11);
- depositing a protective film (passivation layer 27) over the substrate (11) to cover the switching device;
- defining a contact hole (28) in the protective film (27) to expose the drain electrode (23) of the switching device;
- forming pixel electrode (29) to connect the drain electrode via the contact hole (28);
- forming the pixel electrode (29) in a vacuum chamber.

Applicant admitted prior art does not expressly disclose forming the pixel

Art Unit: 2871

electrode by placing the substrate in a vacuum chamber and injecting Hydrogencontaining gas at a temperature of less than 400 °C.

However, Tran discloses (col.2, line 20 - col.3, line 5) forming an electrically conductive oxide composition used as a light transmissive electrode in a device, such as liquid crystal displays, at temperature from about 20 °C to about 300 °C with stabilizing gas such as H₂ or H₂O (Hydrogen-containing gas), and such that preventing the damage by high temperature process.

The pixel electrode also is a conductive electrode. The forming process for a conductive electrode is also suitable for the pixel electrode in order to prevent the damage by high temperature process.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to form the pixel electrode by placing the substrate in a vacuum chamber and injecting hydrogen-containing gas at temperature of less than about 400 °C as claimed in claims 1 and 13 for preventing the damage of a device during the temperature process.

Claims 4-5, Tran discloses (col.4, lines 24-44) that preferably, sputter depositing occurs at temperature of from 25 °C to 150 °C, so that means the device damage would be prevented better in this temperature range during the temperature process.

Therefore, when forming the pixel electrode, the substrate using a temperature process less than 200 °C, and preferably using a temperature between about 50 °C and about 150 °C would have been at least obvious for achieving a better protection during the temperature process.

Art Unit: 2871

Claims 6 and 15, Applicant admitted prior art discloses (page 1, paragraph 0003 - page 4, paragraph 0012; Figs.1A – 1D) forming a gate electrode (13) over the substrate (11); entirely depositing a gate insulating film (15) over the substrate (11) to cover the gate electrode (13); and continuously depositing an active layer (17) and an ohmic contact layer (19) to overlap the gate electrode (13).

Claims 7-9 and 16, Applicant admitted prior art discloses (page 1, paragraph 0003 - page 4, paragraph 0012; Figs.1A – 1D) that the passivation layer (27) is made from an inorganic insulating material such as silicon nitride, silicon oxide, etc., or an organic insulating material such as acrylic, polytetrafluoroethylene, benzocyclobutene, fluoropolymer resin and perfluorocyclobutane, etc.

Claims 10-11 and 17, Applicant admitted prior art discloses (page 1, paragraph 0003 - page 4, paragraph 0012; Figs.1A – 1D) that the pixel electrode (29) is formed from the transparent conductive material such as indium tin oxide (ITO), tin oxide (TO) or indium zinc oxide (IZO).

Claims 12 and 18, Applicant admitted prior art discloses (page 1, paragraph 0003 - page 4, paragraph 0012; Figs.1A – 1D) that the source and drain electrodes (21,23) of the switching device is formed from the metallic thin film such as Mo, Cr, Ti, or Ta, etc., or a molybdenum alloy such as MoW, MoTa or MoNb, etc.

3. Claims 2-3 and 14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant admitted prior art and Tran as applied to claims 1, 4-12, 15-18 above, and further in view of US 6,433,842 (Kaneko et al).

Claims 2-3 and 14, Kaneko discloses (col.5, lines 47 – 51) that the amorphous

Art Unit: 2871

Page 5

indium tin oxide (ITO) or indium zinc oxide (IZO) is preferably used as the material of the pixel electrodes, because the amorphous structure allows for use of a weak acide etchant, so that the aluminum alloy is prevented from being damaged during etching of the pixel electrodes. Kaneko also discloses (col.9, lines 7 – 43) that by using the weak acide, the layered structure underlying the ITO film is secured from being damaged during the etching of the ITO, so that the electrodes underlying the pixel electrodes (ITO) would be secured from being damaged during the etching of the ITO process. Therefore, it would have been obvious to those skilled in the art at the time the invention was made to use amorphous structure as the pixel electrode and use weak acide etchant during etching process as claimed in claims 2-3 and 14 for securing the electrodes underlying the pixel electrodes from being damaged (such as the electrode erosion) during the etching of the ITO.

Art Unit: 2871

Conclusion

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mike Qi whose telephone number is (703) 308-6213.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Mike Qi March 8, 2003

